



## RC15S01 THRU RC15S10

SILICON SILASTIC  
CELL RECTIFIER

TECHNICAL  
SPECIFICATION

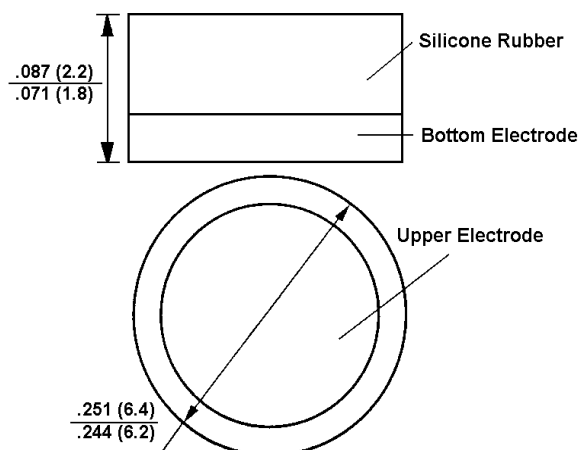
**VOLTAGE: 100 TO 1000V CURRENT: 15A**

### FEATURES

- Low cost
- High surge capability
- Solderable electrode surfaces
- Ideal for hybrids

### MECHANICAL DATA

- Polarity: Bottom or upper electrode denotes cathode according to the notice in package



Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

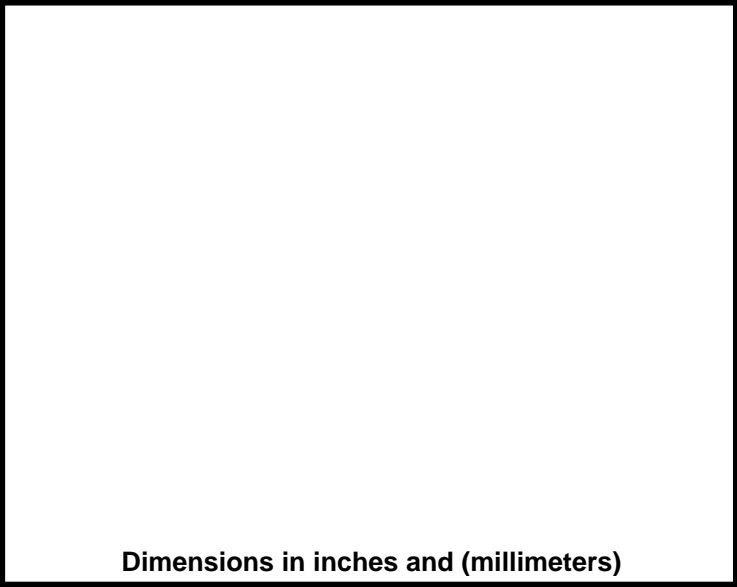
(Single-phase, half-wave, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	RC15S01	RC15S02	RC15S04	RC15S06	RC15S08	RC15S10
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	100	200	400	600	800	1000
Maximum RMS Voltage	$V_{RMS}$	70	140	280	420	560	700
Maximum DC Blocking Voltage	$V_{DC}$	100	200	400	600	800	1000
Maximum Average Forward Rectified Current ( $T_a=55^\circ\text{C}$ ) (Note 2)	$I_{F(AV)}$	15					
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	$I_{FSM}$	400					
Maximum Instantaneous Forward Voltage (at rated forward current)	$V_F$	0.95					
Maximum DC Reverse Current (at rated DC blocking voltage) $T_a=25^\circ\text{C}$ $T_a=150^\circ\text{C}$	$I_R$	10 500					
Typical Junction Capacitance (Note 1)	$C_J$	300					
Typical Thermal Resistance (Note 3)	$R_{\theta(ja)}$	1					
Storage and Operation Junction Temperature	$T_{STG}, T_J$	-50 to +150					

Note:

1. Measured at 1 MHz and applied voltage of 4.0V<sub>dc</sub>
2. When mounted to heat sink from body.
3. Thermal resistance from junction to ambient.

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UNITS
V
V
V
A
A
V
μA
μA
pF
°C/W
°C